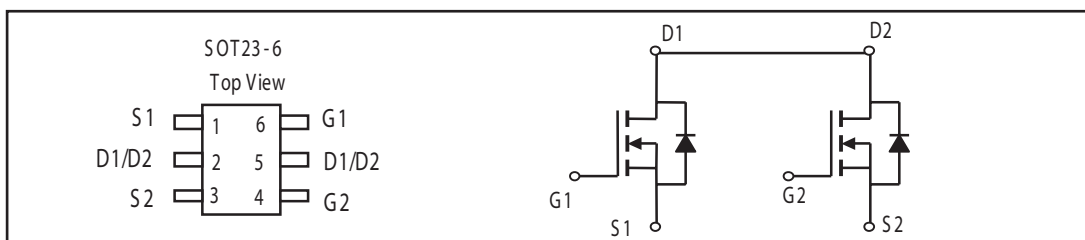


Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(ON)} (m ohm)Max
20V	5A	25@V _{GS} = 4.5 V 40@V _{GS} = 2.5 V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous @ T _J =25 °C -Pulsed ^b	I _D	5	A
	I _{DM}	25	A
Drain-Source Diode Forward Current ^a	I _S	2	A
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	100	°C/W
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